

Abstract

A process for reducing the level(s) of water and/or other impurities from cyclosiloxanes by either azeotropic distillation, or by contacting the cyclosiloxane compositions with an adsorbent bed material. The purified cyclosiloxane material is useful for forming low-dielectric constant thin films having dielectric constants of less than 3.0, more preferably 2.8 to 2.0.